

(12) **United States Patent**  
**Friedrich et al.**

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(54) **MAGNETIC FIELD SENSING ELEMENT  
COMBINING A CIRCULAR VERTICAL HALL  
MAGNETIC FIELD SENSING ELEMENT  
WITH A PLANAR HALL ELEMENT**

(58) **Field of Classification Search**  
CPC ..... G01R 33/07  
USPC ..... 324/251  
See application file for complete search history.

(71) Applicant: **Allegro MicroSystems, LLC,**  
Worcester, MA (US)

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*Primary Examiner* — Bot Ledynh

(74) *Attorney, Agent, or Firm* — Daly, Crowley, Mofford and Durkee, LLP

(57) **ABSTRACT**

A magnetic field sensor includes a circular vertical Hall (CVH) sensing element and at least one planar Hall element. The CVH sensing element has contacts arranged over a common implant region in a substrate. In some embodiments, the at least one planar Hall element is formed as a circular planar Hall (CPH) sensing element also having contacts disposed over the common implant region. A CPH sensing element and a method of fabricating the CPH sensing element are separately described.

**24 Claims, 8 Drawing Sheets**

(72) Inventors: **Andreas P. Friedrich**, Metz-Tessy (FR);  
**Andrea Foletto**, Annecy (FR); **Gary T. Pepka**, Pembroke, NH (US)

(73) Assignee: **ALLEGRO MICROSYSTEMS, LLC,**  
Worcester, MA (US)

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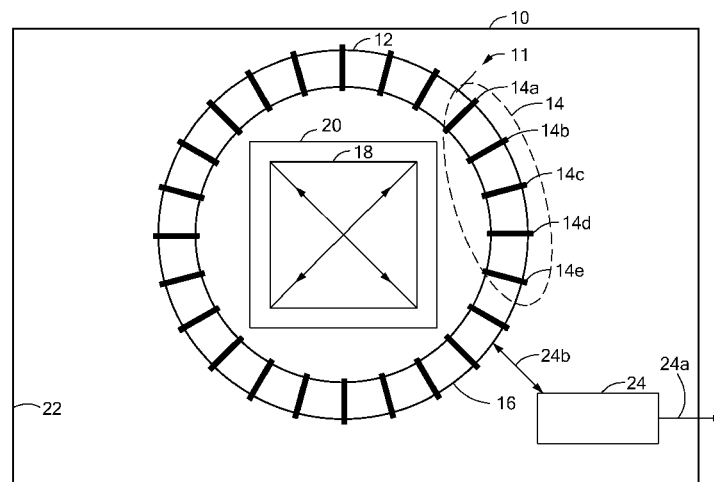
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**G01R 33/00** (2006.01)  
**H01L 43/06** (2006.01)

(52) **U.S. Cl.**  
CPC ..... **G01R 33/072** (2013.01); **G01R 33/0052**  
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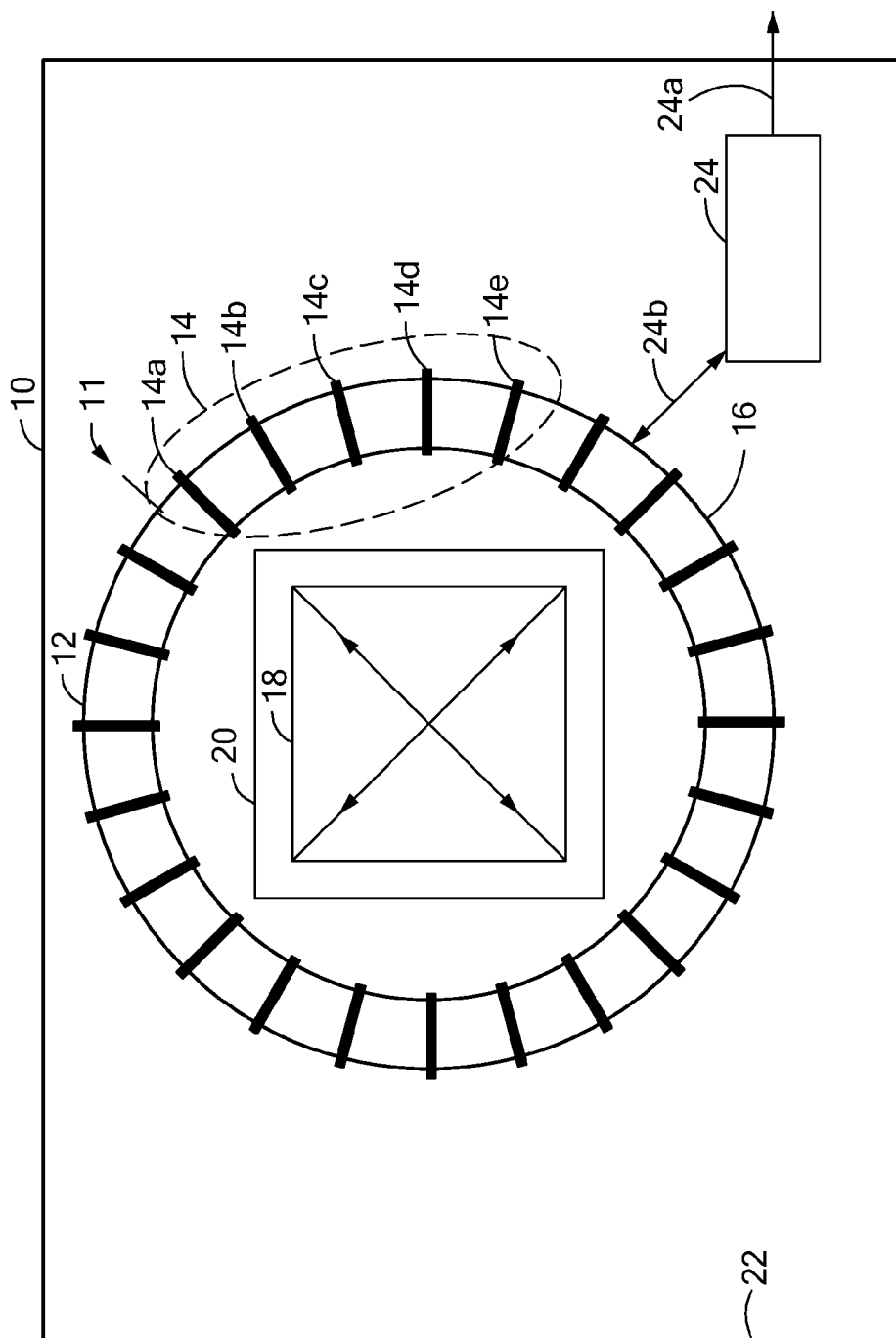


FIG. 1

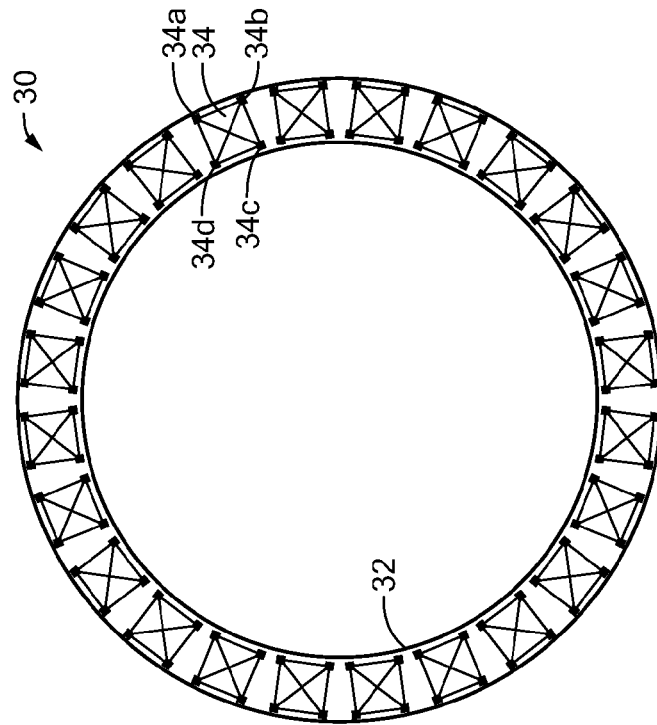


FIG. 2A

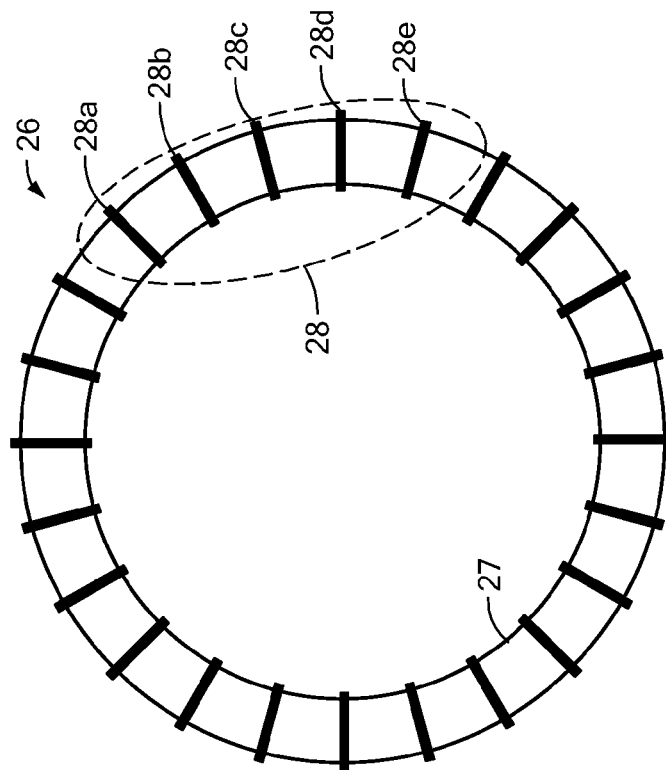


FIG. 2

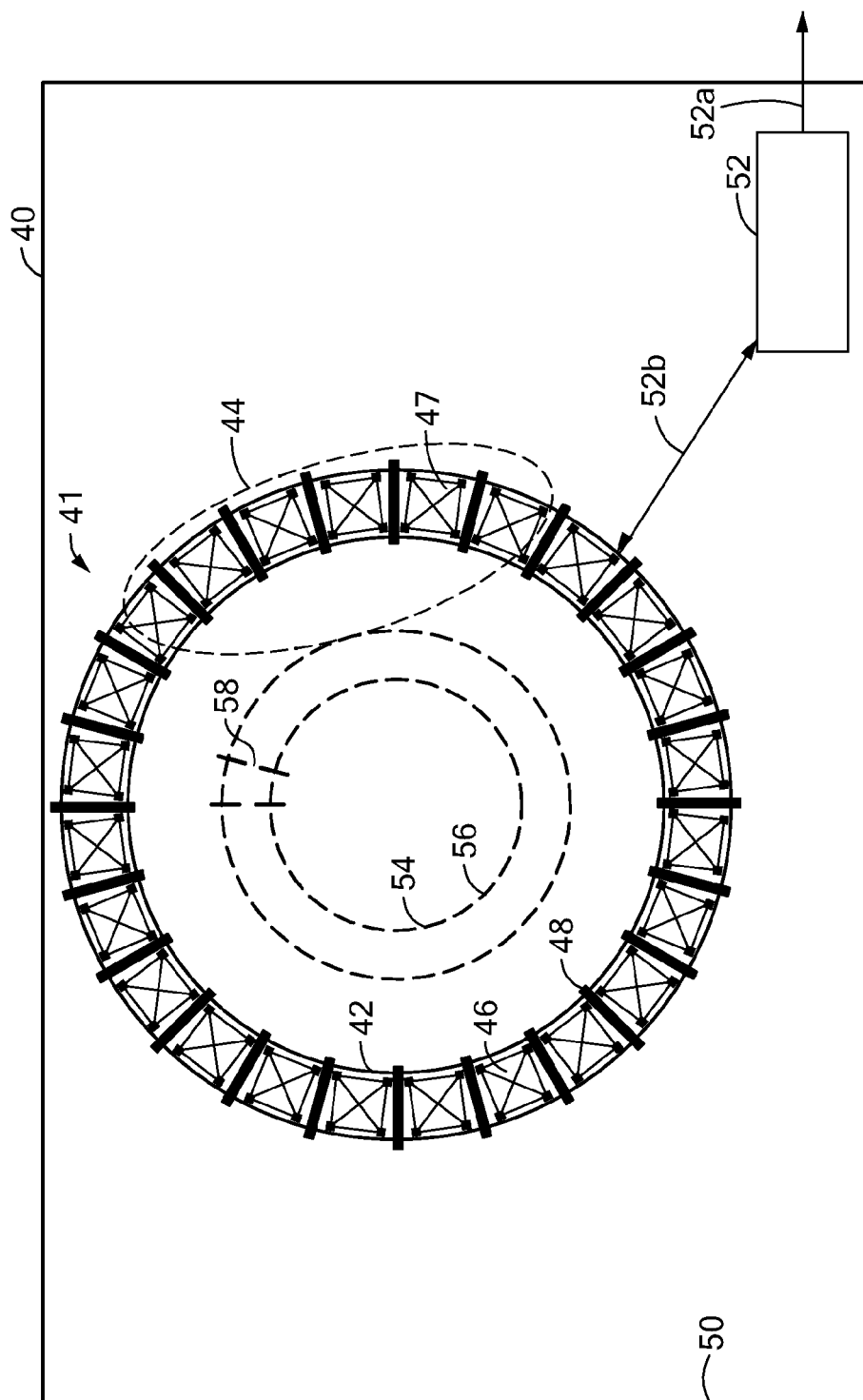


FIG. 2B

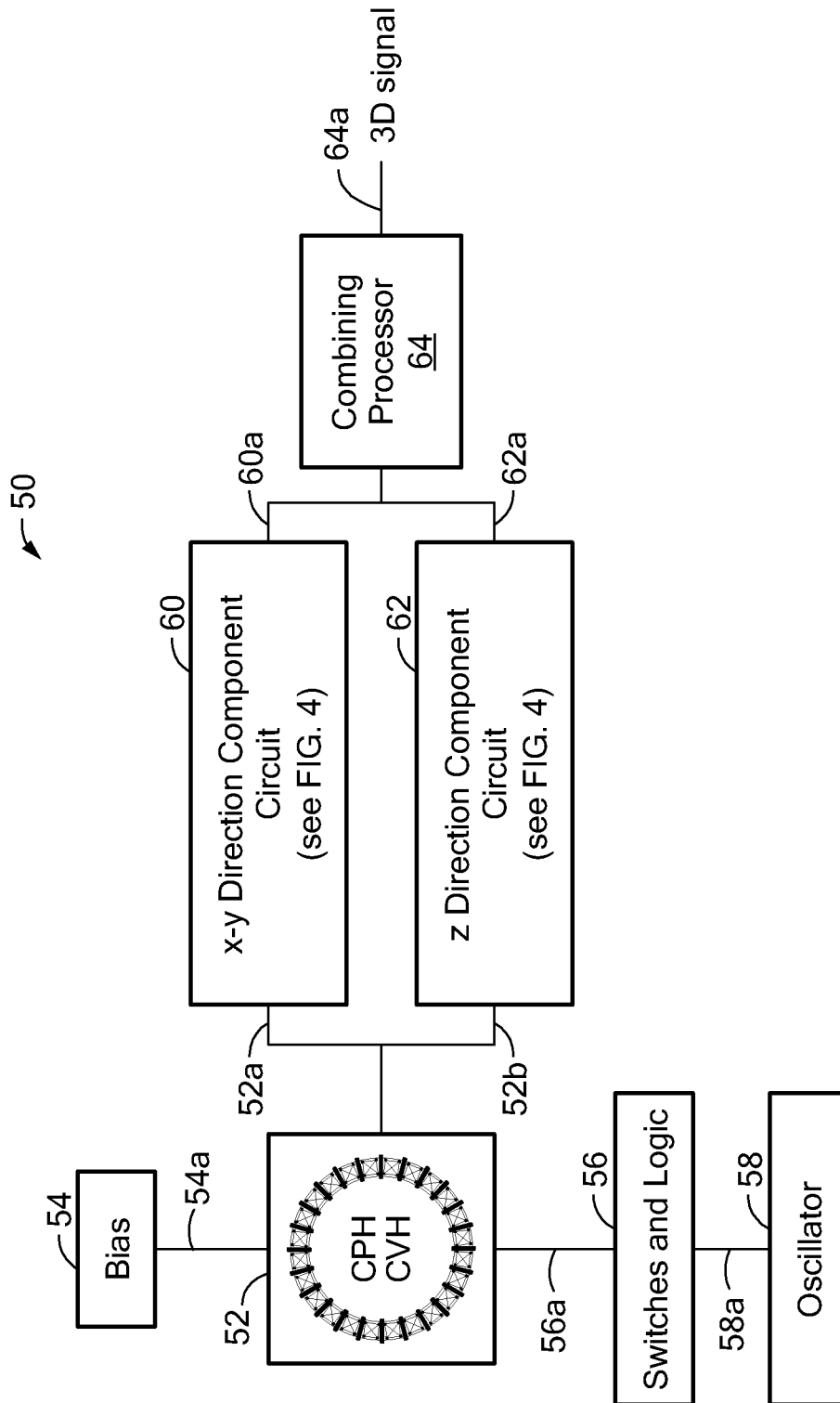


FIG. 3



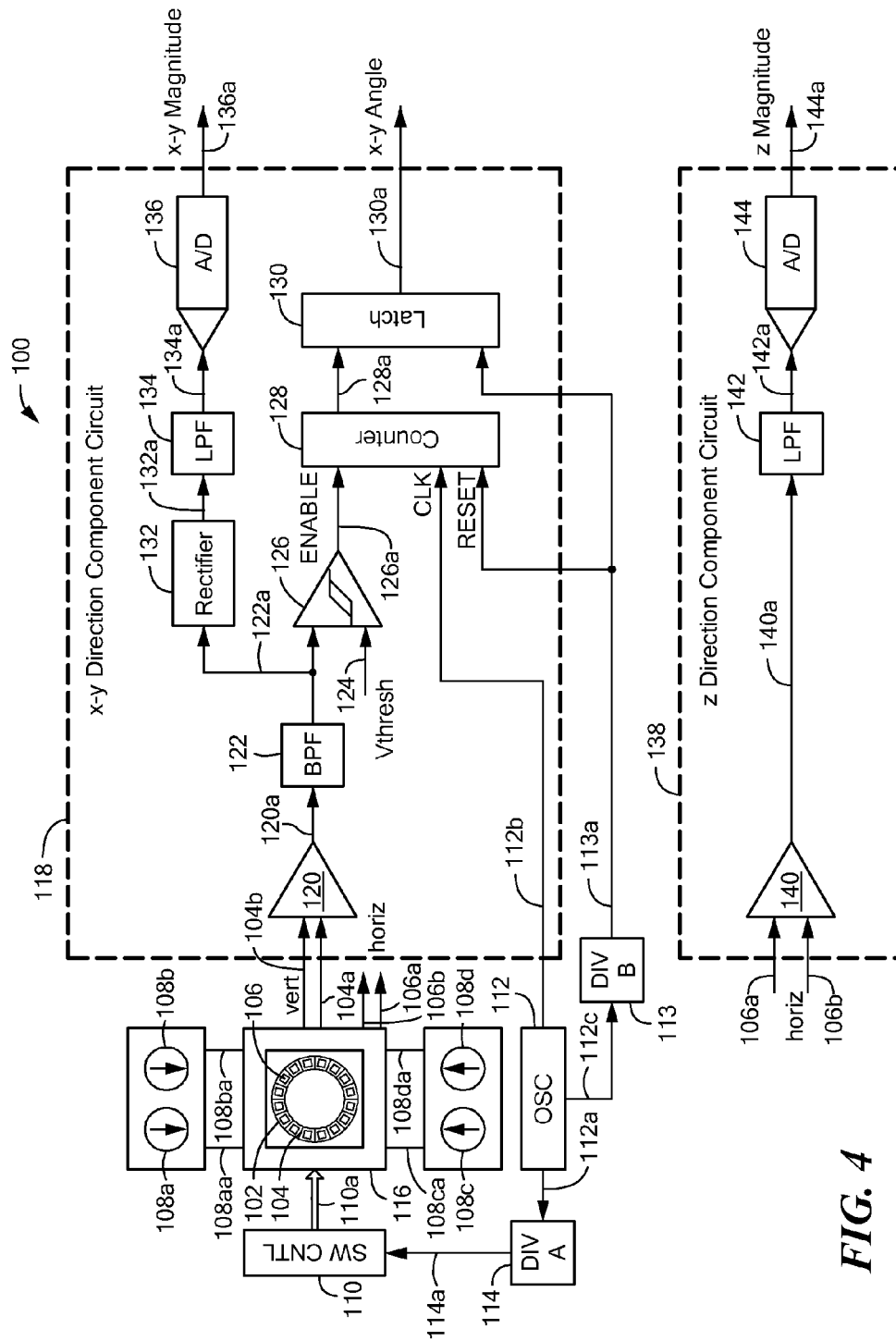
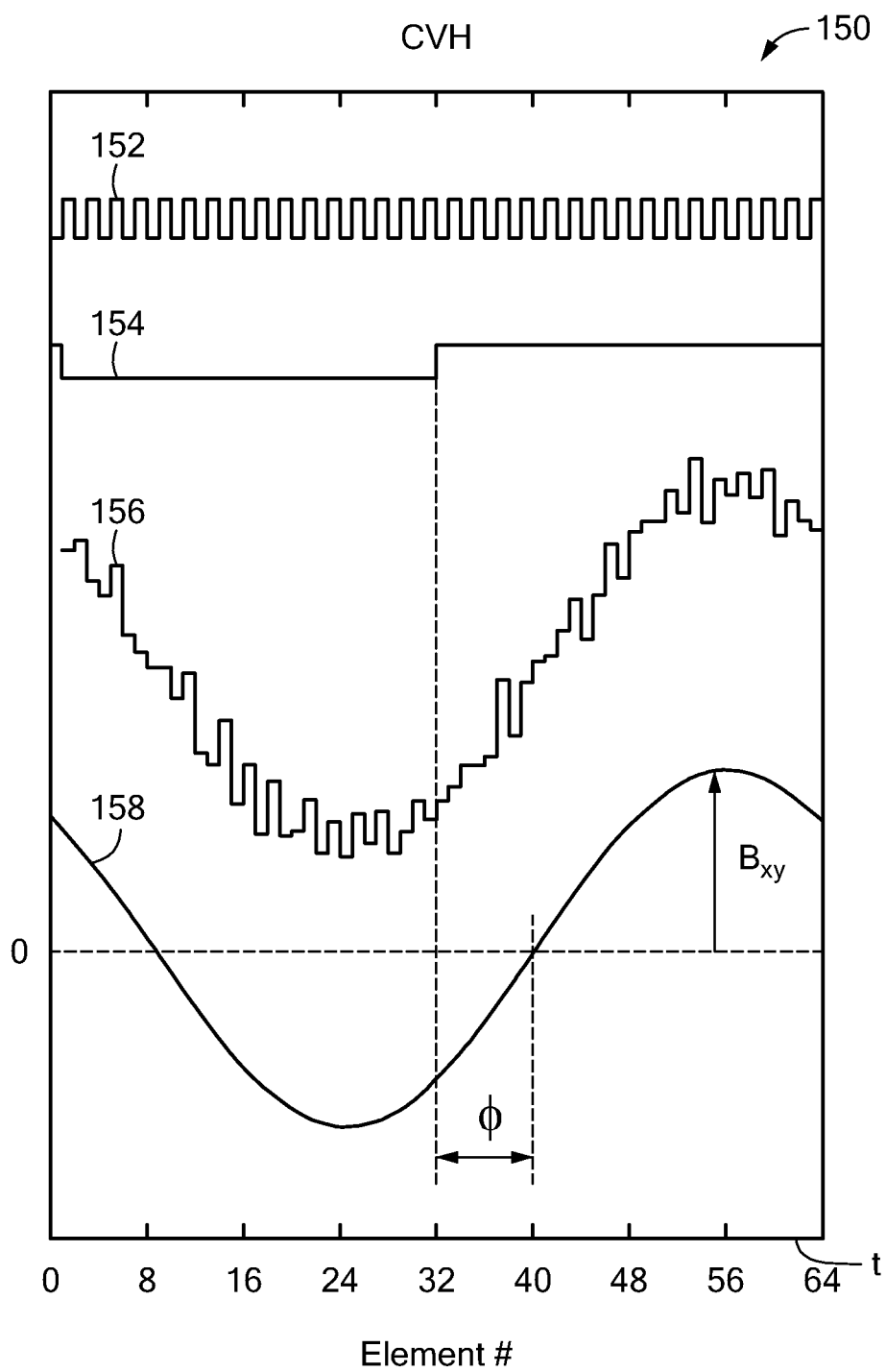
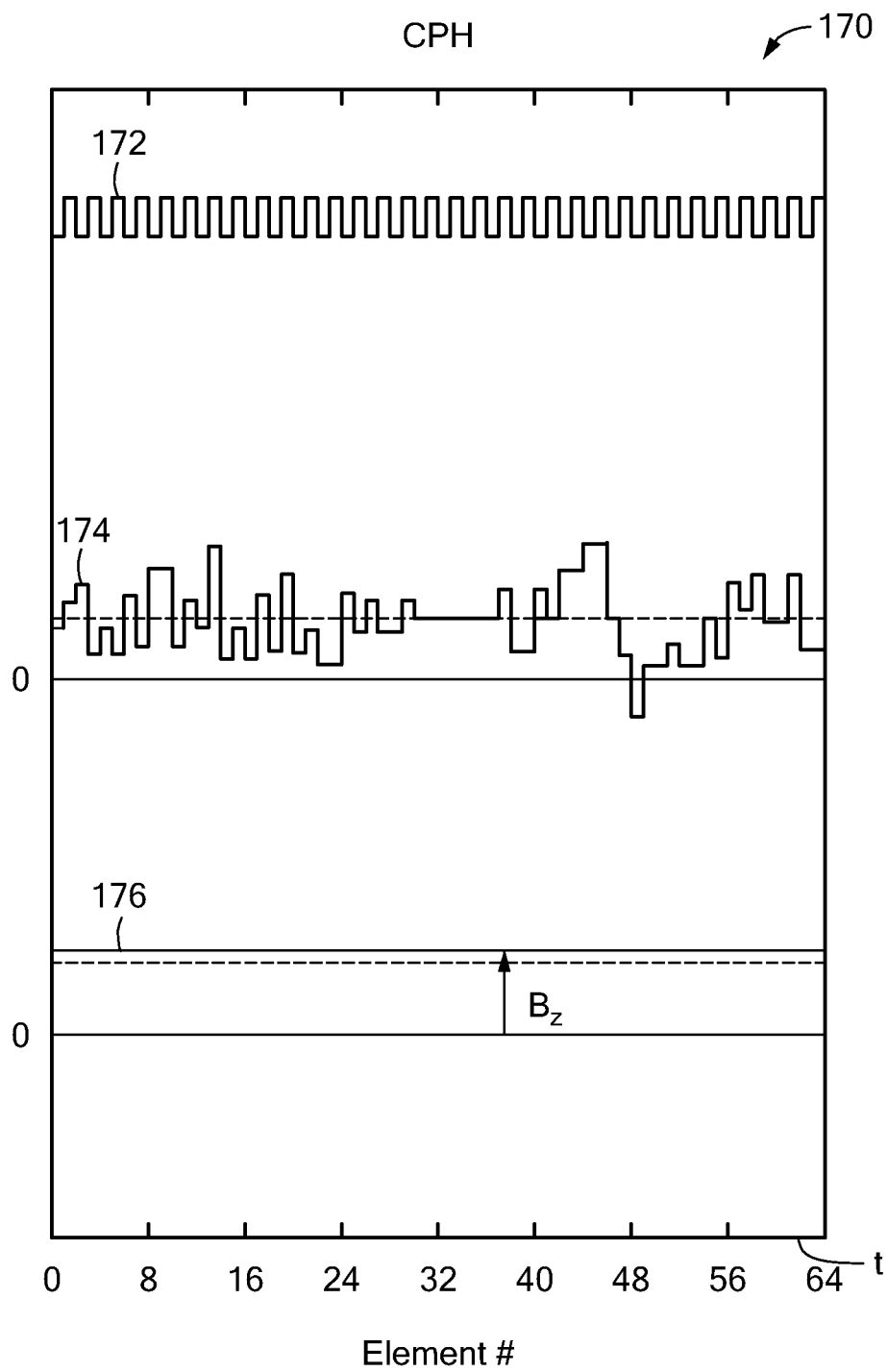


FIG. 4



**FIG. 5**



**FIG. 6**

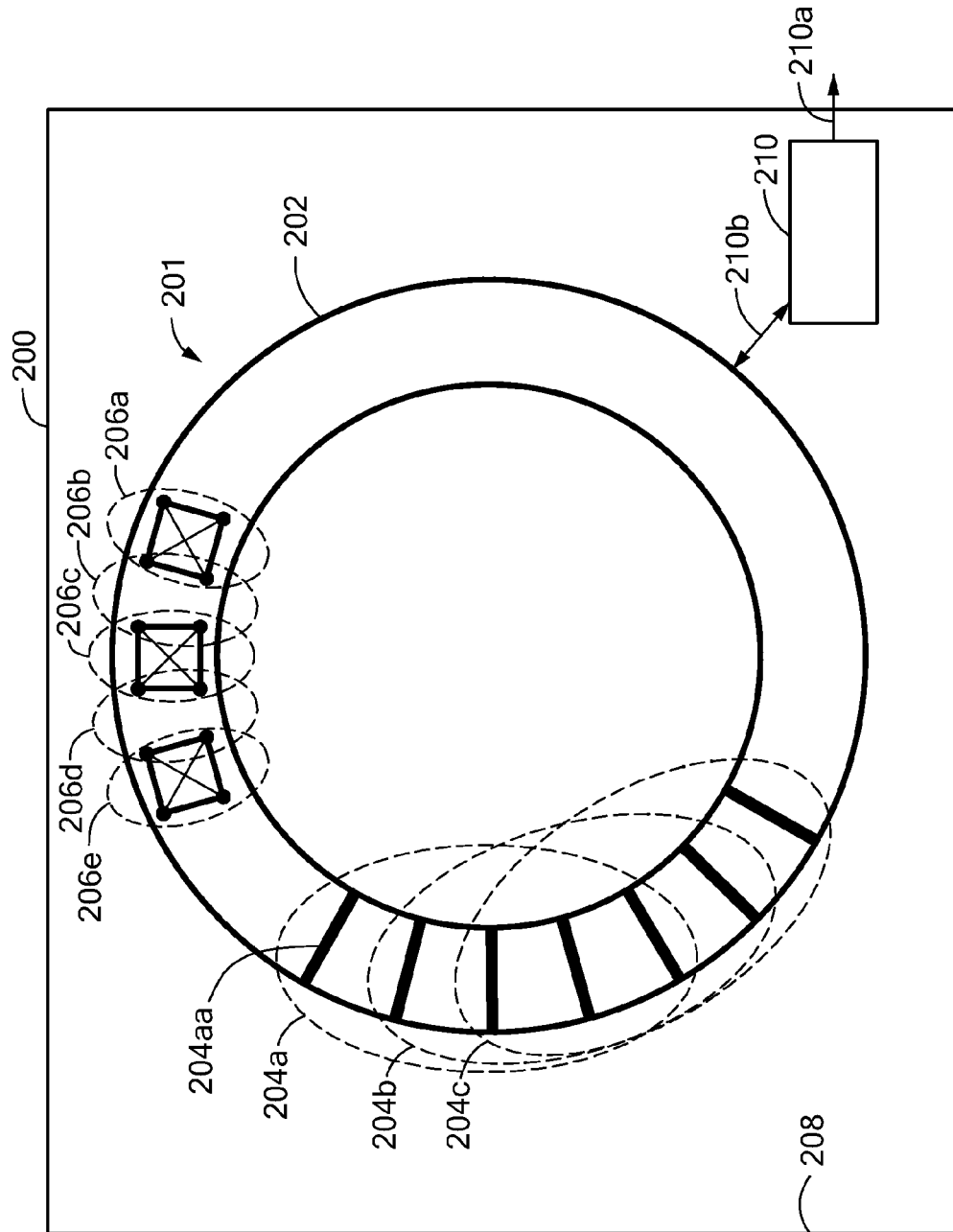


FIG. 7

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# **MAGNETIC FIELD SENSING ELEMENT COMBINING A CIRCULAR VERTICAL HALL MAGNETIC FIELD SENSING ELEMENT WITH A PLANAR HALL ELEMENT**

## **CROSS REFERENCE TO RELATED APPLICATIONS**

This application is a Divisional Application of and claims the benefit of and priority to U.S. patent application Ser. No. 13/226,694 filed Sep. 7, 2011, which is incorporated herein by reference in its entirety.

## **STATEMENT REGARDING FEDERALLY SPONSORED RESEARCH**

Not Applicable.

## **FIELD OF THE INVENTION**

This invention relates generally to magnetic field sensing elements for sensing a direction of a magnetic field and, more particularly, to a magnetic field sensing that combines a circular vertical Hall (CVH) magnetic field sensing element with a planar Hall element.

## **BACKGROUND OF THE INVENTION**

Various types of magnetic field sensing elements are known, including Hall effect elements and magnetoresistance elements. Magnetic field sensors generally include a magnetic field sensing element and other electronic components.

Some magnetic field sensing elements and associated magnetic field sensors provide an electrical signal representative of a direction of a sensed magnetic field. The magnetic field signal varies in accordance with the direction in a way that can be resolved to identify a pointing direction of the magnetic field.

Most types of such direction-indicating magnetic field sensing elements and associated magnetic field sensors generate signals that are indicative of the direction of a component of the magnetic field in only two dimensions, i.e., in a plane. However, the magnetic field may have a pointing direction not parallel to the plane of sensitivity of the magnetic field sensor, i.e., in three dimensions.

Magnetic field sensor that can sense three dimensions of a magnetic field are useful in some applications, for example, in three dimensional joysticks, where the joystick can be moved in two dimensions and also can be depressed in a third dimension. Some three-dimensional applications use both a magnetic field sensor operable to provide a two-dimensional indication of a pointing direction of a magnetic field in a plane and also a separate one-dimensional magnetic field sensor operable to provide indication of a magnitude of a magnetic field in a direction perpendicular to the plane.

Thus, to resolve some of the three-dimensional characteristics of the magnetic field, some arrangements use both a two-dimensional magnetic field sensor and also a one-dimensional magnetic field sensor. In some applications, output signals from the two magnetic field sensors can be further processed to provide a signal representative of a magnitude of the magnetic field along the three-dimensional pointing direction of the magnetic field. Thus, by combining information generated by the two magnetic field sensors, three-dimensional characteristics of the magnetic field can be determined.

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It is cumbersome to provide both the above-described two-dimensional magnetic field sensor and also the above-described one-dimensional magnetic field sensor. A combination of two such magnetic field sensors tends to be expensive. Furthermore, additional processing is required to resolve the three-dimensional characteristics of the sensed magnetic field. Still further, alignment of the two types of magnetic field sensors to provide orthogonal axes is critical to the accuracy of the resulting resolved three-dimensional characteristics, and such alignment can be difficult and inaccurate.

Therefore, it would be desirable to provide a single integrated magnetic field sensing element and associated magnetic field sensor that can generate a signal or signals that is/are indicative of characteristics of a magnetic field in three dimensions. In some embodiments, the integrated magnetic field sensing element is formed upon a single substrate, e.g., a silicon substrate, which tends to make it easier to provide aligned axes.

## **SUMMARY OF THE INVENTION**

The present invention provides a single integrated magnetic field sensing element and associated magnetic field sensor that can generate a signal or signals that is/are indicative of characteristics of a magnetic field in three dimensions. In some embodiments, the integrated magnetic field sensing element is formed upon a single substrate, e.g., a silicon substrate, which tends to make it easier to provide aligned axes.

In accordance with one aspect of the present invention, a magnetic field sensor includes a semiconductor substrate having first and second parallel major surfaces. The magnetic field sensor includes a plurality of vertical Hall elements arranged as a circular vertical Hall (CVH) structure. Each one of the plurality of vertical Hall elements is arranged upon a common circular implant region in the first major surface of the semiconductor substrate. The plurality of vertical Hall elements is configured to generate a respective plurality of x-y output signals responsive to a magnetic field having a direction component in an x-y plane parallel to the first major surface of the semiconductor substrate, the x-y plane having an x-direction and a direction orthogonal to the x-direction. The magnetic field sensor also includes a planar Hall element disposed upon the semiconductor substrate. The planar Hall element is configured to generate a z output signal responsive to a magnetic field having a direction component in a z direction orthogonal to the x-y plane. The magnetic field sensor also includes a processing circuit disposed upon the semiconductor substrate, coupled to receive a signal representative of the plurality of x-y output signals, coupled to receive a signal representative of the z output signal, configured to generate one or more of an x-y angle signal representative of an angle of the direction component in the x-y-plane, or an x-y magnitude signal representative of a magnitude of the direction component in the x-y plane, and configured to generate a z magnitude signal representative of a magnitude of the direction component in the z direction.

In some embodiments, the x-y angle signal, the x-y magnitude signal, and the z-magnitude signal can be combined to generate a three-dimensional signal representative of a three-dimensional pointing direction of the magnetic field and/or a magnitude of the magnetic field along the three-dimensional pointing direction.

In accordance with another aspect of the present invention, a magnetic field sensor includes a semiconductor substrate having first and second parallel major surfaces parallel to an x-y plane. The magnetic field sensor also includes a plurality

of planar Hall elements arranged as a circular planar Hall (CPH) structure. Each one of the plurality of planar Hall elements is arranged upon a common circular implant region in the first major surface of the semiconductor substrate. The plurality of planar Hall elements is configured to generate a plurality of z output signals responsive to a magnetic field having a direction component in a z direction orthogonal to the x-y plane.

In accordance with another aspect of the present invention, a method of fabricating a magnetic field sensing element arrangement includes forming a common circular implant region in a first major surface of a semiconductor substrate having the first and a second major parallel surface both parallel to an plane. The method also includes forming, over the common circular implant region, a plurality of planar Hall elements arranged as a circular planar Hall (CPH) structure. The plurality of planar Hall elements is configured to generate a plurality of z output signals responsive to a magnetic field having a direction component in a z direction orthogonal to the x-y plane.

#### BRIEF DESCRIPTION OF THE DRAWINGS

The foregoing features of the invention, as well as the invention itself may be more fully understood from the following detailed description of the drawings, in which:

FIG. 1 is a pictorial showing a magnetic field sensor having a magnetic field sensing element arrangement with a circular vertical Hall (CVH) sensing element and a planar Hall element disposed over separate implant regions in a common substrate;

FIG. 2 is a pictorial showing a CVH sensing element having a plurality of vertical Hall elements, each vertical Hall element having a plurality of vertical Hall element contacts;

FIG. 2A is a pictorial showing a circular planar Hall (CPH) sensing element having a plurality of planar Hall elements, each planar Hall element having a plurality of planar Hall element contacts;

FIG. 2B is a pictorial showing a magnetic field sensing element arrangement having a CVH sensing element and having a CPH sensing element all disposed over a common implant region in a common substrate;

FIG. 3 is a block diagram showing a magnetic field sensor having a magnetic field sensing element arrangement with the CVH sensing element and with a CPH sensing element in a combined arrangement, having an x-y direction component circuit, having a z direction component circuit, and having a combining circuit;

FIG. 4 is a block diagram showing further details of the magnetic field sensor of FIG. 3;

FIG. 5 is a graph showing four signals within the magnetic field sensor of FIG. 4 and associated with the CVH sensing element;

FIG. 6 is a graph showing mother three signals within the magnetic field sensor of FIG. 4 and associated with the CPH sensing element; and

FIG. 7 is a pictorial showing magnetic field sensor having a magnetic field sensing element arrangement with a CVH sensing element and a CPH sensing element.

#### DETAILED DESCRIPTION OF THE INVENTION

Before describing the present invention, some introductory concepts and terminology are explained.

As used herein, the term “magnetic field sensing element” is used to describe a variety of electronic elements that can sense a magnetic field. The magnetic field sensing elements

can be, but are not limited to, Hall effect elements, magnetoresistance elements, or magnetotransistors. As is known, there are different types of Hall effect elements, for example, a planar Hall element, a vertical Hall element, and a circular Hall element. As is also known, there are different types of magnetoresistance elements, for example, a giant magnetoresistance (GMR) element, an anisotropic magnetoresistance element (AMR), a tunneling magnetoresistance (TMR) element, an Indium antimonide (InSb) sensor, and a magnetic tunnel junction (MTJ).

A so-called “circular vertical Hall” (CVH) sensing element, is known and described in PCT Patent Application No. PCT/EP2008056517, entitled “Magnetic Field Sensor for Measuring Direction of a Magnetic Field in a Plane,” filed May 28, 2008, and published in the English language as PCT Publication No. WO 2008/145662, which application and publication thereof are incorporated by reference herein in their entirety. The CM sensing element is a circular arrangement of vertical Hall elements (i.e., vertical Hall element contacts) arranged over a common circular implant region in a substrate. The CVH sensing element can be used to sense a direction (i.e., an angle), and optionally a magnitude, of a component of a magnetic field in a plane of the substrate.

As is known, some of the above-described magnetic field sensing elements tend to have an axis of maximum sensitivity parallel to a substrate that supports the magnetic field sensing element, and others of the above-described magnetic field sensing elements tend to have an axis of maximum sensitivity perpendicular to a substrate that supports the magnetic field sensing element. In particular, planar Hall elements tend to have axes of sensitivity perpendicular to a substrate, while magnetoresistance elements and vertical Hall elements (including circular vertical Hall (CVH) sensing elements) tend to have axes of sensitivity parallel to a substrate.

Magnetic field sensors are used in a variety of applications, including, but not limited to, an angle sensor that senses an angle of a direction of a magnetic field, a current sensor that senses a magnetic field generated by a current carried by a current-carrying conductor, a magnetic switch that senses the proximity of a ferromagnetic object, a rotation detector that senses passing ferromagnetic articles, for example, magnetic domains of a ring magnet, and a magnetic field sensor that senses a magnetic field density of a magnetic field.

Referring to FIG. 1, a magnetic field sensor 10 can include a magnetic field sensing element arrangement 11. The magnetic field sensing element arrangement 11 includes a circular vertical Hall (CVH) sensing element 12 disposed over a common implant region 16, which is disposed upon a substrate 22. The CVH sensing element 12 includes a plurality of vertical Hall elements, of which a vertical Hall element 14 is but one example. The vertical Hall element 14, like other vertical Hall elements in the CVH sensing element 12, includes a plurality of vertical Hall element contacts, of which vertical Hall element contacts 14a, 14b, 14c, 14d, 14e are examples. While the vertical Hall element 14 is shown having five vertical Hall element contacts 14a, 14b, 14c, 14d, 14e, in other embodiments, a CVH sensing element can have vertical Hall elements with more than five or fewer than five vertical Hall element contacts, for example, four vertical Hall element contacts or six vertical Hall element contacts.

The magnetic field sensing element arrangement 11 can also include a planar Hall element 18 disposed upon the substrate 22, for example in the center or near the center of the CVH sensing element 12. However, other placements of the planar Hall element 18 upon the substrate 22 are also possible. The planar Hall element 18 is disposed over a separate implant region 20.

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The CVH sensing element **12** in conjunction with electronics **24**, described more fully below, can provide an output signal **24a** representative of one or more two dimensional aspects of a magnetic field. The one or more aspects can include, for example, a) an angle of a direction of a component of a magnetic field experienced by the CVH sensing element **12** in a plane of the CVH sensing element **12**, and b) a magnitude of the magnetic field in the plane of the CVH sensing element **12**.

In contrast, the planar Hall element **18** in conjunction with the electronics **24** can provide the output signal **24a** representative of a magnitude of a component of the magnetic field in a direction perpendicular to a plane of the planar Hall element **18**.

With the above information, the magnetic field sensing element arrangement **11** in conjunction with the electronics **24** can provide sufficient information to resolve some three-dimensional characteristics of the magnetic field, for example, a) a three-dimensional pointing direction of the magnetic field experienced by the magnetic field sensing element arrangement **10**, and b) a magnitude of the magnetic field along the three-dimensional pointing direction. In some embodiments, the resolution of the three-dimensional characteristics can be provided by another processor (not shown) coupled to receive the signal **24a**. However, in some embodiments, the electronics **24** can provide the output signal **24a** representative of the three-dimensional pointing direction of the magnetic field and also the magnitude of the magnetic field in the three-dimensional pointing direction.

Referring now to FIG. 2, a CVH sensing element **26** having a plurality of vertical Hall elements, of which a vertical Hall element **28** is but one example, can be the same as or similar to the CVH sensing element **12** of FIG. 1. The CVH sensing element **26** can include a common implant region **27** in a substrate over which the plurality of vertical Hall elements, each having a plurality of vertical Hall element contacts, are disposed. Each vertical Hall element, for example, a vertical Hall element **28**, can include a plurality of vertical Hall element contacts, for example, five contacts, **28a**, **28b**, **28c**, **28d**, **28e**.

Referring now to FIG. 2A, a circular planar Hall (CPH) sensing element **30** can include a plurality of planar Hall elements, of which a planar Hall element **34** is but one example. The planar Hall elements can be disposed over a common implant region **32** in a substrate. Each planar Hall element, for example, the planar Hall element **34**, can include a plurality of planar Hall element contacts, for example four contacts, **34a**, **34b**, **34c**, **34d**.

Referring now to FIG. 2B, a magnetic field sensor **40** can include a magnetic field sensing element arrangement **41**. The magnetic field sensing element arrangement **41** can include a CVH sensing element **48**, which can be the same as or similar to the CVH sensing element **26** of FIG. 2, and also a CPH sensing element **46**, which can be the same as or similar to the CPH sensing elements **30** of FIG. 2A. The CVH sensing element **48**, which includes a plurality of vertical Hall elements, of which a vertical Hall element **44** is but one example, is disposed over a common implant region **42** upon a substrate **50**. Also, the CPH sensing element **46**, which includes a plurality of planar Hall elements, of which a planar Hall element **47** is but one example, is also disposed over the common implant region **42** upon the substrate **50**. Each one of the planar Hall elements of the CPH sensing element **46** can be disposed between contacts of the CVH sensing element.

It will be appreciated that, like the magnetic field sensor **10** of FIG. 1, the magnetic field sensor **40** can include electronics **52**, described more fully below, that can provide an output

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signal **52a** representative of one or more two and/or three-dimensional characteristics of a magnetic field experienced by the magnetic field sensor **40**. For example, the output signal **52a** can provide information representative of one or more of a) an angle of a direction of a component of a magnetic field experienced by the magnetic field sensing element arrangement **41** in a plane of the CVH sensing element **48**, b) a magnitude of the component of the magnetic field in the plane of the CVH sensing element **48**, c) a magnitude of a component of the magnetic field in a direction perpendicular to a plane of the CPH sensing element **46**, d) a three-dimensional pointing direction of the magnetic field experienced by the magnetic field sensing element arrangement **41**, and e) a magnitude of the magnetic field along the three-dimensional pointing direction.

In some alternate embodiments, the CVH sensing element **48** and the CPH sensing element **46** are disposed over different implant regions. In some alternate embodiments, there are fewer planar Hall elements such that a planar Hall element is not disposed between every pair of vertical Hall element contacts.

Shown optionally, by way of phantom lines, as described above, instead of the CVH sensing element **48**, the sensing element arrangement **41** can have a Mill sensing element **54** disposed over a separate common implant region **56**, separate from the common implant region **42** over which the CPH sensing element **46** is disposed. In the CVH sensing element **54**, only two vertical Hall element contacts, e.g., **58**, are shown for clarity.

While the optional CVH sensing element **54** is shown to have a smaller diameter disposed over a smaller diameter common implant region than the CPH sensing element **46**, in other embodiments, an optional CVH sensing element can have a larger diameter and be disposed over a larger diameter common implant region than the CPH sensing element **46**. In some embodiments, the optional CVH sensing element **54** is disposed on an opposite side of the substrate **50** from the CPH sensing element **46**.

Referring now to FIG. 3, a magnetic field sensor **50** can include a magnetic field sensing element arrangement **52**, which can include a combination of a CVH sensing element and a CPH sensing element like the magnetic field sensing element arrangement **41** of FIG. 2B. In other embodiments, the magnetic field sensing element arrangement **52** can be like the magnetic field sensing element arrangement **11** of FIG. 1.

An oscillator **58** is configured to generate a clock signal **58a**. Switches and logic **56** are coupled to provide control signals **56a** to the magnetic field sensing element arrangement **52**. The switching and control of a CVH sensing element are described more fully in the above-mentioned PCT Patent Application No. PCT/EP2008056517. Switching and control of a CPH sensing element is similar to that of a CVH sensing element. Both are described more fully below in conjunction with FIG. 7.

A bias circuit **54** is configured to provide one or more bias signals **54a** to the magnetic field sensing element arrangement **52**. In some embodiments, the one or more bias signals **54a** are current signals.

The magnetic field sensing element arrangement **52** is configured to generate an output signal **52a** representative of an angle and a magnitude of a component of the magnetic field experienced by the magnetic field sensing element arrangement **52** in a plane (an x-y plane) of the magnetic field sensing element arrangement **52**. The magnetic field sensing element arrangement **52** is also configured to generate an output signal **52b** representative of a magnitude of a component of the magnetic field experienced by the magnetic field sensing

element arrangement **52** in a direction perpendicular to the plane of magnetic field sensing element arrangement **52**.

An x-y direction component circuit **60** is coupled to receive the signal **52a** and configured to generate a signal **60a** representative of the angle of the component of the magnetic field experienced by the magnetic field sensing element arrangement **52**, and can be representative of the magnitude of the component of the magnetic field in the plane of the magnetic field sensing element arrangement **52**. A z direction component circuit **62** is coupled to receive the signal **52h** and configured to generate a signal **62a** representative of the magnitude of the component of the magnetic field experienced by the magnetic field sensing element arrangement **52** in the direction perpendicular to the plane of the sensing element and arrangement **52**.

A combining processor **64** is coupled to receive the signals **60a**, **62a**, and configured to generate an output signal **64a**, which can be signal representative of all of the above directional characteristics. In some embodiments, the output signal can also or instead be representative of a three-dimensional pointing direction of the magnetic field and/or a magnitude of the magnetic field along the three-dimensional pointing direction.

Operation of the magnetic field sensor **50** is more fully described below in conjunction with FIG. 4.

Referring now to FIG. 4, a magnetic field sensor **100** includes a magnetic field sensing element arrangement **102** having a CVH sensing element **104** with a plurality of vertical Hall elements and a CPH sensing element **106** with a plurality of planar Hall elements, like the magnetic field sensing element arrangement **41** of FIG. 2B. In other embodiments, the magnetic field sensing element arrangement **102** can be like the magnetic field sensing element arrangement **11** of FIG. 1.

Current sources **108a**, **108b**, **108c**, **108d** can provide bias signals in the form of current signals **108aa**, **108ba**, **108ca**, **108da** to the magnetic field sensing element arrangement **102**.

An oscillator **112** can generate a clock signal **112a**. A divider **114** can be coupled to receive the clock signal **112a** and configured to generate a divided clock signal **114a**. A switch control circuit **110** can be coupled to receive the divided clock circuit **114a** and configured to generate control signals **110a**. A switching circuit **116** is coupled to receive the control signals **110a** and configured to operate the magnetic field sensing element arrangement **102** in ways more fully described below.

Operation of the CVH sensing element part **104** of the magnetic field sensing element arrangement **102** is more fully described in the above-described PCT Publication No. WO 2008/145662.

The magnetic field sensing element arrangement **102**, and, in particular, the CVH sensing element **104**, is configured to generate a differential signal **104a**, **104b**, which includes a plurality of so-called "x-y output signals." The magnetic field sensing element arrangement **102**, and, in particular, the CPH sensing element **106**, is also configured to generate a differential signal **106a**, **106b**, which includes a plurality of so-called "z output signals."

The magnetic field sensor **100** can include an x-y direction component circuit **118**, which can be the same as or similar to the x-y direction component circuit **60** of FIG. 3. The x-y direction component circuit **118** can include an amplifier **120** coupled to receive the differential signal **104a**, **104b** and configured to generate an amplified signal **120a** (also referred to herein as a first intermediate signal). A bandpass filter **122** is coupled to receive the amplified signal **120a** and configured

to generate a filtered signal **122a**. A comparator **126**, with or without hysteresis, is coupled to receive the filtered signal **122a**. The comparator **126** is also coupled to receive a threshold signal **124**. The comparator **126** is configured to generate a thresholded signal **126a** responsive to a comparison between the filtered signal **122a** and a threshold signal **124**.

The x-y direction component circuit **118** can also include a counter **128** coupled to receive the thresholded signal **126a** at an enable input.

The oscillator **112** is also configured to generate clock signals **112b** and **112c**. A divider **113** is coupled to receive the clock signal **112c** and configured to generate another divided clock signal **113a**.

The counter **128** is coupled to receive the clock signal **112b** at a clock input and coupled to receive the divided clock signal **113a** at a reset input.

In operation, the counter **128** is configured to generate a count signal **128a**, which is a multi-bit digital signal representative of a phase difference between the thresholded signal **126a** and the divided clock signal **113a**. Thus, the count signal **128a** is representative of an angle of a direction of a component of the magnetic field experienced by the CVH sensing element **104** in a plane of the CVH sensing element **104**, which is also referred to herein as an x-y plane.

The x-y direction component circuit **118** can also include a latch **130** coupled to receive the count signal **128a** and configured to generate a latched signal **130a**, which, like the count signal **128a**, is representative of the angle of the direction of the component of the magnetic field experienced by the CVH sensing element **104** in the x-y plane of the CVH sensing element **104**.

The x-y direction component circuit **118** can also include an amplitude detection circuit. The amplitude detection circuit can include a rectifier **132** coupled to receive the filtered signal **122a** and configured to generate a rectified signal **132a**. The amplitude detection circuit can also include a low pass filter **134** coupled to receive the rectified signal **132a** and configured to generate a low pass filtered signal **134a**. An analog-to-digital converter **136** can be coupled to receive the low pass filtered signal **134a** and configured to generate a signal **136a**, which is representative of a magnitude the component of the magnetic field experienced by the CVH sensing element **104** in the x-y plane. Other circuit topologies can also be used to detect amplitude.

The magnetic field sensor **100** can also include a z direction component circuit **138** having an amplifier **140** coupled to receive the differential signal **106a**, **106b**. The amplifier **140** is configured to generate an amplified signal **140a** (also referred to herein as a second intermediate signal). A low pass filter **142** is coupled to receive the amplified signal **140a** and configured to generate a filtered signal **142a**. An analog-to-digital converter **144** is coupled to receive the filtered signal **142a** and configured to generate a z magnitude signal **144a**, which is representative of a magnitude of a component of the magnetic field experienced by the CPH sensing element **106** in a direction perpendicular to the x-y plane. Other circuit topologies can also be used to detect the z-magnitude.

The signals **136a**, **130a**, **144a** can be provided to a combining processor, for example, the combining processor **64** of FIG. 3. In some embodiments, the combining processor is configured to format one or more of the signals **130a**, **136a**, **144a** into a standard format for communication to circuits outside of the magnetic field sensor. The format can be one of a variety of formats, including, but not limited to, a SENT format, an I2C format, or a pulse width modulated (PWM) format. In other embodiments, the combining processor is further configured to process the signals **130a**, **136a**, **144a** to



generate one or more of a signal representative of a pointing direction of the magnetic field in three dimensions, for example, an angle relative to the x-y plane, or a signal representative of a magnitude of the magnetic field signal along the three-dimensional pointing direction. These signals can also be put into one of the above standard formats for communication with the above-described signals or in place of the above-described signals.

Referring now to FIG. 5, a graph 150 has a horizontal axis with units representative of a vertical Hall element position around the CVH sensing element 104 of FIG. 4. Vertical Hall element position is discussed more fully below in conjunction with FIG. 7. As will be understood from discussion below in conjunction with FIG. 7, in an exemplary embodiment there can be sixty-four vertical Hall element contacts in the CVH sensing element 104 and a corresponding sixty-four vertical Hall elements in the CVH sensing element 104.

The graph 150 also includes a vertical axis having units of volts in four different ranges corresponding to four different signals 152, 154, 156, 158.

The signal 152 is representative of the clock signal 112b of FIG. 4. The signal 154 is representative of the divided clock signal 113a of FIG. 4. The signal 156 is representative of the amplified signal 120a of FIG. 4. The signal 158 is representative of the filtered signal 122a of FIG. 4.

It should be understood that the signal 154 is a fixed reference signal that does not change phase in relation to a direction of a magnetic field. However, the signals 156 and 158 do change phase in relation to the direction of the magnetic field in the plane of a corresponding CVH sensing element. The phase difference between that of the signal 154 and that of the signals 156, 158 is representative of an angle of the magnetic field in a plane of the CVH sensing element.

From the signal 158, it can be seen that different ones of the vertical Hall elements within the CVH sensing element 104 provide signals with different amplitudes relative to zero when in the presence of a magnetic field. A maximum negative signal is achieved at vertical Hall element position number 24 and a maximum positive signal is achieved at vertical Hall element position number 56. A phase of the signal 158, i.e., a sensing element position of the maxima and minima, is related to the angle of the direction of a component of the magnetic field experienced by the CVH sensing element 104 in the plane of the CVH sensing element 104 (FIG. 4). Thus, for other angles of the magnetic field, the phase will be different, and the maxima and minima (and also the zero crossings) will be at different vertical Hall element positions.

With regard to the signal 156, the irregular up-and-down excursions of the signal 156 are representative of DC offset signals that vary among the vertical Hall elements of the CVH sensing element 104. The offset voltages are undesirable.

A magnitude  $B_{xy}$  of the signal 158 is representative of the magnitude of the component of the magnetic field experienced by the CVH sensing element 104 of FIG. 4 in the plane of the CVH sensing element 104.

Referring now to FIG. 6, graph 170 has a horizontal axis with units representative of a planar Hall element position around the CPH sensing element 106 of FIG. 4. As will be understood from discussion below in conjunction with FIG. 7, in an exemplary embodiment there can be sixty-four planar Hall elements in the CPH sensing element 106 and two hundred fifty six planar Hall element contacts in the CPH sensing element 106.

The graph 170 also includes a vertical axis having units of volts in three different ranges corresponding to three different signals 172, 174, 176.

The signal 172, like the signal 152 of FIG. 5, is representative of the clock signal 112b of FIG. 4. The signal 174 is representative of the amplified signal 140a of FIG. 4. The signal 176 is representative of the filtered signal 142a of FIG. 4.

A magnitude  $B_z$  of the signal 176 is representative of a magnitude of a component of the magnetic field experienced by the CPH sensing element 106 in a direction perpendicular to the plane of the CPH sensing element 106.

Referring now to FIG. 7, a magnetic field sensor 200 includes a magnetic field sensing element arrangement 201. The magnetic field sensing element arrangement 201 includes a circular implant region 202 in a surface of a substrate 208. A plurality of vertical Hall elements, of which vertical Hall elements 204a, 204b, 204c are examples, is disposed upon the circular implant region 202. Each vertical Hall element has a plurality of Hall element contacts (e.g., four or five contacts), of which a vertical Hall element contact 204aa is but one example.

A particular vertical Hall element (e.g., 204a) within the CVH sensing, which, for example, can have five adjacent contacts, can share some, for example, four, of the five contacts with a next vertical Hall element (e.g., 204b). Thus, a next vertical Hall element 204b can be shifted by one contact from a prior vertical Hall element. For such shifts by one contact, it will be understood that the number of vertical Hall elements is equal to the number of vertical Hall element contacts, e.g., sixty-four. However, it will also be understood that a next vertical Hall element can be shifted by more than one contact from the prior vertical Hall element, in which case, there are fewer vertical Hall elements than there are vertical Hall element contacts in the CVH sensing element.

In an exemplary CM sensing element, there are sixty-four vertical Hall elements and sixty-four vertical Hall element contacts. However, a CVH can have more than or fewer than sixty-four vertical Hall elements and more than or fewer than sixty-four vertical Hall element contacts.

The magnetic field sensing element arrangement 201, like the magnetic field sensing element arrangement 41 of FIG. 2B, can also include a plurality of planar Hall elements, for example, planar Hall elements 206a, 206b, 206c, 206d, 206e.

Each planar Hall element can have, for example, four contacts, which are represented by dots. In some embodiments contacts of planar Hall elements are essentially shared. For example, in one embodiment a first planar Hall element 206a has four contacts. A next planar Hall element 206b shares two of the contacts of the planar Hall element 206a. A next planar Hall element 206c shares two of the contacts of the planar Hall element 206b, and so on.

In other embodiments, contacts of adjacent planar Hall elements are not shared. For example, a first planar Hall element 206a can share no contacts with a next planar Hall element 206c.

In some embodiments, each vertical Hall element (e.g., five vertical Hall element contacts) is chopped. Chopping will be understood to be a switching arrangement that reconfigures the current drive signals to the contacts of a vertical Hall element and reconfigures the output signal contacts of a vertical Hall element, most often in four configurations, one at a time, to provide an output signal from the vertical Hall element sequentially representative of the four configurations. Chopping tends to result in a reduction of the effect of offset voltages of the vertical Hall elements discussed above in conjunction with the signal 156 of FIG. 5.

Similarly, in some embodiments, each planar Hall element (e.g., four planar Hall element contacts) is chopped to achieve the same benefit. However, in other embodiments no chop-

ping is used, in which case, only one configuration of drive and output contacts is used for each vertical or planar Hall element.

While sixty-four vertical Hall elements and sixty-four planar Hall elements are described in CVH and CPH sensing elements above, it will be understood that there can be more than or fewer than sixty-four or either type of Hall elements in the magnetic field sensing element arrangements described above, including embodiments that have unequal numbers of vertical Hall elements

All references cited herein are hereby incorporated herein by reference in their entirety. Having described preferred embodiments, which serve to illustrate various concepts, structures and techniques, which are the subject of this patent, it will now become apparent to those of ordinary skill in the art that other embodiments incorporating these concepts, structures and techniques may be used. Accordingly, it is submitted that that scope of the patent should not be limited to the described embodiments but rather should be limited only by the spirit and scope of the following claims.

What is claimed is:

1. A magnetic field sensing element arrangement, comprising:

- a semiconductor substrate having first and second parallel major surfaces parallel to an x-y plane;
- a plurality of planar Hall elements arranged as a circular planar Hall (CPH) structure, wherein each one of the plurality of planar Hall elements is arranged upon a common circular implant region in the first major surface of the semiconductor substrate, wherein the plurality of planar Hall elements is configured to generate a plurality of z output signals responsive to a magnetic field having a direction component in a z direction orthogonal to the x-y plane; and
- a processing circuit disposed upon the semiconductor substrate and coupled to receive a signal representative of the plurality of z output signals, wherein each one of the plurality of planar Hall elements comprises a respective group of planar Hall element contacts, wherein the processing circuit is operable to process the plurality of planar Hall elements using a plurality of groups of the planar Hall element contacts to generate the signal representative of the plurality of z output signals, the processing circuit comprising a z direction component processor coupled to receive the signal representative of the plurality of z output signals and configured to generate an intermediate signal responsive to the direction component of the magnetic field in the z direction, wherein the intermediate signal comprises a DC signal component having a DC signal value responsive to a magnitude of the direction component of the magnetic field in the z direction, wherein the processing circuit is operable to generate an output signal indicative of the magnitude of the direction component of the magnetic field in the z direction responsive to the DC signal value.

2. A magnetic field sensing element arrangement, comprising:

- a semiconductor substrate having first and second parallel major surfaces parallel to an x-y plane;
- a plurality of planar Hall elements arranged as a circular planar Hall (CPH) structure, wherein each one of the plurality of planar Hall elements is arranged upon a common circular implant region in the first major surface of the semiconductor substrate, wherein the plurality of planar Hall elements is configured to generate a plurality of z output signals responsive to a magnetic

field having a direction component in a z direction orthogonal to the x-y plane; and

- a circular vertical Hall (CVH) sensing element disposed upon the common circular implant region, wherein the CVH sensing element comprises a plurality of vertical Hall element contacts, and wherein the plurality of planar Hall elements includes individual planar Hall elements interposed with the vertical Hall element contacts.

3. A magnetic field sensing element arrangement, comprising:

- a semiconductor substrate having first and second parallel major surfaces parallel to an x-y plane;
- a plurality of planar Hall elements arranged as a circular planar Hall (CPH) structure, wherein each one of the plurality of planar Hall elements is arranged upon a common circular implant region in the first major surface of the semiconductor substrate, wherein the plurality of planar Hall elements is configured to generate a plurality of z output signals responsive to a magnetic field having a direction component in a z direction orthogonal to the x-y plane; and
- a circular vertical Hall (CVH) sensing element disposed upon a different common circular implant region in a major surface of the semiconductor substrate, wherein the CVH sensing element comprises a plurality of vertical Hall element contacts.

4. A method of fabricating a magnetic field sensing element arrangement, the method comprising:

- forming a common circular implant region in a first major surface of a semiconductor substrate having the first and a second major parallel surface both parallel to an x-y plane;
  - forming, over the common circular implant region, a plurality of planar Hall elements arranged as a circular planar Hall (CPH) structure, wherein the plurality of planar Hall elements is configured to generate a plurality of z output signals responsive to a magnetic field having a direction component in a z direction orthogonal to the x-y plane; and
  - forming a circular vertical Hall (CVH) sensing element disposed upon the common circular implant region, wherein the CVH sensing element comprises a plurality of vertical Hall element contacts, and wherein the plurality of planar Hall elements includes individual planar Hall elements interposed with the vertical Hall element contacts,
- wherein the common circular implant region comprises a common semiconducting region disposed beneath the plurality of planar Hall elements.

5. A method of fabricating a magnetic field sensing element arrangement, the method comprising:

- forming a common circular implant region in a first major surface of a semiconductor substrate having the first and a second major parallel surface both parallel to an x-y plane;
- forming, over the common circular implant region, a plurality of planar Hall elements arranged as a circular planar Hall (CPH) structure, wherein the plurality of planar Hall elements is configured to generate a plurality of z output signals responsive to a magnetic field having a direction component in a z direction orthogonal to the x-y plane; and
- forming a circular vertical Hall (CVH) sensing element disposed upon a different common circular implant region in a major surface of the semiconductor substrate, wherein the CVH sensing element comprises a plurality of vertical Hall element contacts,

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wherein the common circular implant region comprises a common semiconducting region disposed beneath the plurality of planar Hall elements.

6. The magnetic field sensing element arrangement of claim 1, wherein the common circular implant region comprises n-type doping material and wherein the substrate is comprised of p-type material.

7. The magnetic field sensing element arrangement of claim 1, wherein the semiconductor substrate comprises a silicon substrate.

8. The magnetic field sensing element arrangement of claim 1, wherein the processing circuit is further operable to process each group of planar Hall element contacts in a multiplexed arrangement, wherein different ones of the planar Hall element contacts of each one of the plurality of planar Hall elements provide different ones of the plurality of z output signals at different times.

9. The magnetic field sensing element arrangement of claim 1, further comprising a circular vertical Hall (CVH) sensing element disposed upon the common circular implant region, wherein the CVH sensing element comprises a plurality of vertical Hall element contacts, and wherein the plurality of planar Hall elements includes individual planar Hall elements interposed with the vertical Hall element contacts.

10. The magnetic field sensing element arrangement of claim 1, further comprising a circular vertical Hall (CVH) sensing element disposed upon a different common circular implant region in a major surface of the semiconductor substrate, wherein the CVH sensing element comprises a plurality of vertical Hall element contacts.

11. The magnetic field sensor of claim 1, wherein each one of the plurality of planar Hall elements of the CPH structure comprises a respective group of planar Hall element contacts, wherein ones of the plurality of planar Hall elements share planar Hall element contacts with other ones of the plurality of planar Hall elements.

12. The magnetic field sensing element arrangement of claim 2, wherein the common circular implant region comprises n-type doping material and wherein the substrate is comprised of p-type material.

13. The magnetic field sensing element arrangement of claim 2, wherein the semiconductor substrate comprises a silicon substrate.

14. The magnetic field sensing element arrangement of claim 2, further comprising a processing circuit disposed upon the semiconductor substrate and coupled to receive a signal representative of the plurality of z output signals, wherein each one of the plurality of planar Hall elements comprises a respective group of planar Hall element contacts, wherein the processing circuit is operable to process the plurality of planar Hall elements using a plurality of groups of the planar Hall element contacts to generate the signal representative of the plurality of z output signals, wherein the processing circuit is further operable to process each group of planar Hall element contacts in a multiplexed arrangement, wherein different ones of the planar Hall element contacts of each one of the plurality of planar Hall elements provide different ones of the plurality of z output signals at different times.

15. The magnetic field sensing element arrangement of claim 14, wherein the processing circuit comprises a z direction component processor coupled to receive the signal representative of the plurality of z output signals and configured to generate an intermediate signal responsive to the direction component of the magnetic field in the z direction, wherein the intermediate signal comprises a DC signal component having a DC signal value responsive to a magnitude of the direction component of the magnetic field in the z direction,

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wherein the processing circuit is operable to generate an output signal indicative of the magnitude of the direction component of the magnetic field in the z direction responsive to the DC signal value.

16. The magnetic field sensor of claim 2, wherein each one of the plurality of planar Hall elements of the CPH structure comprises a respective group of planar Hall element contacts, wherein ones of the plurality of planar Hall elements share planar Hall element contacts with other ones of the plurality of planar Hall elements.

17. The magnetic field sensing element arrangement of claim 3, wherein the common circular implant region comprises n-type doping material and wherein the substrate is comprised of p-type material.

18. The magnetic field sensing element arrangement of claim 3, wherein the semiconductor substrate comprises a silicon substrate.

19. The magnetic field sensing element arrangement of claim 3, further comprising a processing circuit disposed upon the semiconductor substrate and coupled to receive a signal representative of the plurality of z output signals, wherein each one of the plurality of planar Hall elements comprises a respective group of planar Hall element contacts, wherein the processing circuit is operable to process the plurality of planar Hall elements using a plurality of groups of the planar Hall element contacts to generate the signal representative of the plurality of z output signals.

20. The magnetic field sensing element arrangement of claim 19, wherein the processing circuit is further operable to process each group of planar Hall element contacts in a multiplexed arrangement, wherein different ones of the planar Hall element contacts of each one of the plurality of planar Hall elements provide different ones of the plurality of z output signals at different times.

21. The magnetic field sensing element arrangement of claim 19, wherein the processing circuit comprises a z direction component processor coupled to receive the signal representative of the plurality of z output signals and configured to generate an intermediate signal responsive to the direction component of the magnetic field in the z direction, wherein the intermediate signal comprises a DC signal component having a DC signal value responsive to a magnitude of the direction component of the magnetic field in the z direction, wherein the processing circuit is operable to generate an output signal indicative of the magnitude of the direction component of the magnetic field in the z direction responsive to the DC signal value.

22. The magnetic field sensor of claim 3, wherein each one of the plurality of planar Hall elements of the CPH structure comprises a respective group of planar Hall element contacts, wherein ones of the plurality of planar Hall elements share planar Hall element contacts with other ones of the plurality of planar Hall elements.

23. The method of claim 4, wherein each one of the plurality of planar Hall elements of the CPH structure comprises a respective group of planar Hall element contacts, the method further comprising:

sharing planar Hall element contacts between ones of the plurality of planar Hall elements.

24. The method of claim 5, wherein each one of the plurality of planar Hall elements of the CPH structure comprises a respective group of planar Hall element contacts, the method further comprising:

sharing planar Hall element contacts between ones of the plurality of planar Hall elements.

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 9,411,023 B2  
APPLICATION NO. : 14/550202  
DATED : August 9, 2016  
INVENTOR(S) : Andreas Friedrich et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Specification

Column 1, Line 47 delete “field sensor” and replace with -- field sensors --.

Column 2, Line 42 delete “a direction orthogonal orthogonal” and replace with -- a y-direction orthogonal --.

Column 3, Line 13 delete “parallel surface” and replace with -- parallel surfaces --.

Column 3, Line 14 delete “to an plane.” and replace with -- to an x-y plane. --.

Column 3, Line 31 delete “substrate,” and replace with -- substrate; --.

Column 3, Line 33 delete “a. plurality” and replace with -- a plurality --.

Column 3, Line 41 delete “a CPU sensing element” and replace with -- a CPH sensing element --.

Column 3, Line 54 delete “showing mother” and replace with -- showing another --.

Column 3, Line 57 delete “showing magnetic. field” and replace with -- showing a magnetic field --.

Column 4, Line 16 delete “Publication No,” and replace with -- Publication No. --.

Column 4, Line 18 delete “The CM” and replace with -- The CVH --.

Column 4, Line 45 delete “arrangement 11, The” and replace with -- arrangement 11. The --.

Column 4, Line 47 delete “vertical Ball” and replace with -- vertical Hall --.

Signed and Sealed this  
Tenth Day of January, 2017



Michelle K. Lee  
*Director of the United States Patent and Trademark Office*

Column 5, Line 55 delete “elements 30” and replace with -- element 30 --.

Column 5, Line 63 delete “the CPU sensing” and replace with -- the CPH sensing --.

Column 5, Line 67 delete “more filly” and replace with -- more fully --.

Column 6, Line 24 delete “a mill” and replace with -- a CVH --.

Column 7, Line 4 delete “a signal 60 a” and replace with -- a signal 60a --.

Column 7, Line 8 delete “and can he” and replace with -- and can be --.

Column 7, Line 12 delete “52h” and replace with -- 52b --.

Column 7, Line 20 delete “characteristics, In” and replace with -- characteristics. In --.

Column 7, Line 33 delete “can he like” and replace with -- can be like --.

Column 7, Line 44 delete “110a, A” and replace with -- 110a. A --.

Column 8, Line 35 delete “signal 132a,” and replace with -- signal 132a. --.

Column 9, Line 10 delete “Hail” and replace with -- Hall --.

Column 10, Line 29 delete “he shifted” and replace with -- be shifted --.

Column 10, Line 32 delete “vertical. Hall” and replace with -- vertical Hall --.

Column 10, Line 33 delete “CM” and replace with -- CVH --.

Column 10, Line 41 delete “Hail” and replace with -- Hall --.

Column 10, Line 43 delete “embodiments” and replace with -- embodiments, --.

Column 10, Line 67 delete “benefit,” and replace with -- benefit. --.

Column 11, Line 10 delete “elements” and replace with -- elements. --.

Column 11, Line 12 delete “entirety Having” and replace with -- entirety. Having --.